ABSTRACT OF THE DISCLOSURE

Crystal orientation planes exist randomly in a crystalline silicon film manufactured by a conventional method, and the orientation ratio is low with respect to a specific crystal orientation. A semiconductor film having a high orientation ratio for the {101} lattice plane is obtained if crystallization of an amorphous semiconductor film, which has silicon as its main constituent and contains from 0.1 to 10 atom% germanium, is performed after introduction of a metal element. A TFT is manufactured utilizing the semiconductor film.